CMSD2836 CMSD2838

SURFACE MOUNT DUAL SILICON SWITCHING DIODES





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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMSD2836 and CMSD2838 are ultra-high speed silicon switching diodes manufactured by the epitaxial planar process, in an epoxy molded SUPERmini™ surface mount package, designed for high speed switching applications.

The following configurations are available:

CMSD2836 DUAL, COMMOM ANODE MARKING CODE: A2C CMSD2838 DUAL, COMMON CATHODE MARKING CODE: A6C

MAXIMUM RATINGS: (T _A =25°C)	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	75	V
Average Forward Current	IO	200	mA
Peak Forward Current, tp=1.0s	I _{FM}	300	mA
Power Dissipation	P_{D}	275	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	455	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (TA=25°C unless otherwise noted)

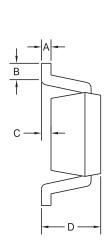
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{R}	V _R =50V			100	nA
BV_R	I _R =100μA	75			V
V_{F}	I _F =10mA			1.0	V
V_{F}	I _F =50mA			1.0	V
V_{F}	I _F =100mA			1.2	V
C_{T}	V _R =0, f=1.0MHz		1.5	4.0	pF
trr	$I_{P}=I_{F}=10\text{mA}$, $I_{rr}=1.0\text{mA}$, $R_{I}=100\Omega$			4.0	ns

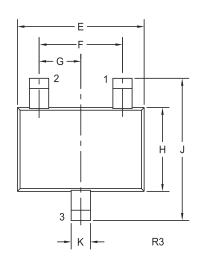
CMSD2836 CMSD2838

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SOT-323 CASE - MECHANICAL OUTLINE

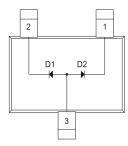




DIMENSIONS						
	INCHES		MILLIMETERS			
SYMBOL	MIN	MAX	MIN	MAX		
Α	0.002	0.008	0.05	0.20		
В	0.004	-	0.10	-		
С	-	0.004	-	0.10		
D	0.031	0.043	0.80	1.10		
E	0.071	0.087	1.80	2.20		
F	0.051		1.30			
G	0.026		0.65			
Н	0.045	0.053	1.15	1.35		
J	0.079	0.087	2.00	2.20		
K	0.008	0.016	0.20	0.40		
SUT 333 (DEI/: D3)						

SOT-323 (REV: R3)

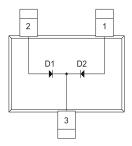
PIN CONFIGURATIONS



CMSD2836

LEAD CODE:

- 1) Cathode D2
- 2) Cathode D1 3) Anode D1, D2
- MARKING CODE: A2C



CMSD2838

LEAD CODE:

- 1) Anode D2
- 2) Anode D1
- 3) Cathode D1, D2

MARKING CODE: A6C

R4 (8-February 2010)